

Docket No.: M4065.0536/P536-B
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Hongmei Wang et al.

Application No.: NOT YET ASSIGNED Art Unit: N/A

Filed: January 6, 2004 Examiner: Not Yet Assigned

For: **FULLY-DEPLETED (FD) (SOI) MOSFET
ACCESS TRANSISTOR AND METHOD OF
FABRICATION**

FIRST PRELIMINARY AMENDMENT

MS Non-Fee Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

Prior to examination on the merits, please amend the above-identified U.S. patent application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks/Arguments begin on page 5 of this paper.